



IFW

Dkt.06080

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

PCT

WERNER BENSCH

Serial No.: 10/586,946

Filed: July 25, 2006

For: SEMICONDUCTOR STRUCTURE COMPRISING ACTIVE ZONES

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Applicant submits herewith a copy of a reference for consideration by the Examiner, which is listed on the attached Form PTO-1449.

Respectfully submitted,

Malcolm J. MacDonald

Malcolm J. MacDonald
Registration No. 40250

LAW OFFICES
DENNISON, SCHULTZ & MACDONALD
SUITE 105
1727 KING STREET
ALEXANDRIA, VIRGINIA 22314-2700
703 837-9600

Form PTO-1449

ATTY DOCKET NO.
0608095

APPLICATION No.
10/586,946

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets ~~if~~ necessary)

APPLICANT
Werner Bensch

FILING DATE
July 25, 2006

GROUP
PCT

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

		Contour et al, "(GaAl) As Tunnel Junctions Grown by Molecular Beam Epitaxy: Intercell OHMIC Contacts for multiple-Band-Gap Solar Cells" Solar Cells Switzerland, 1984, pp. 667-76.

EXAMINER /Shouxiang Hu/

DATE CONSIDERED 01/30/2009

EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /S.H./